A B S T R A C T

METHOD FOR EPIREADY SURFACE TREATMENT ON SIC THIN FILMS

The invention concerns a method of preparing a wafer of a semiconductor material intended for microelectronics and/or optoelectronics applications. The method comprises a step of annealing the material in an oxidizing atmosphere and a step of polishing with an abrasive based on particles of colloidal silica. The polishing step can be carried out using a polishing head (10), into which the semiconductor material substrate (12) is inserted. The liquid abrasive is injected into the head, for example via a side conduit (18). A pressure (20) and a movement indicated by the arrow (22) are applied to the head (10) to carry out polishing against a polishing pad (14). The combination of these two steps produces a satisfactory surface condition, in particular in the case of silicon carbide.

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